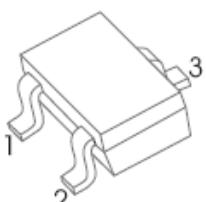


SWITCHING DIODE	SOT-323 Plastic-Encapsulate Diodes				
<p><u>SOT-323</u></p>  <p>Marking :A7t</p>	<p><b>Features</b></p> <ul style="list-style-type: none"> <li>For high-speed switching applications</li> <li>Connected in series</li> </ul>				
<b>Maximum Ratings @Ta=25°C</b>					
Parameter	Symbol	Limit	Unit		
Reverse Voltage	$V_R$	75	V		
Forward Current	$I_F$	150	mA		
Non-Repetitive Peak Forward Surge Current @t=8.3ms	$I_{FSM}$	2.0	A		
Power Dissipation	$P_D$	200	mW		
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	625	°C/W		
Junction Temperature	$T_J$	150	°C		
Storage Temperature range	$T_{STG}$	-55~+150	°C		
<b>ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)</b>					
Parameter	Symbol	Test conditions	Min	Max	Unit
Reverse breakdown voltage	$V_{(BR)}$	$I_R = 100\mu A$	75		V
Reverse voltage leakage current	$I_{R1}$	$V_R = 75V$		2.5	$\mu A$
	$I_{R2}$	$V_R = 25V$		25	nA
Forward voltage	$V_F$	$I_F = 1mA$ $I_F = 10mA$ $I_F = 50mA$ $I_F = 150mA$		715 855 1000 1250	mV
Diode capacitance	$C_D$	$V_R = 0$ f=1MHz		2	pF
Reverse recovery time	$t_{rr}$	$I_F = I_R = 10mA$ $I_{rr} = 0.1 \times I_R R_L = 100\Omega$		4	ns

### Typical Characteristics

